

IGBT - Field Stop, Trench

75 A, 650 V

FGHL75T65LQDT

Description

Field stop 4th generation Low $V_{CE(sat)}$ IGBT technology and Full current rated copak Diode technology.

Features

- Maximum Junction Temperature: $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.15\text{ V (Typ.) @ } I_C = 75\text{ A}$
- 100% Of The Part Are Tested For I_{LM} (Note 2)
- Smooth & Optimized Switching
- Tight Parameter Distribution
- Co-Packed With Soft And Fast Recovery Diode
- RoHS Compliant

Typical Applications

- Solar Inverter
- UPS, ESS
- PFC, Converters

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector to Emitter Voltage	V_{CES}	650	V
Gate to Emitter Voltage	V_{GES}	± 20	V
Transient Gate to Emitter Voltage		± 30	
Collector Current @ $T_C = 25^{\circ}\text{C}$ (Note 1)	I_C	80	A
Collector Current @ $T_C = 100^{\circ}\text{C}$		75	
Pulsed Collector Current (Note 2)	I_{LM}	300	A
Pulsed Collector Current (Note 3)	I_{CM}	300	A
Diode Forward Current @ $T_C = 25^{\circ}\text{C}$ (Note 1)	I_F	80	A
Diode Forward Current @ $T_C = 100^{\circ}\text{C}$		75	
Pulsed Diode Maximum Forward Current	I_{FM}	300	A
Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$	P_D	469	W
Maximum Power Dissipation @ $T_C = 100^{\circ}\text{C}$		234	
Operating Junction Temperature / Storage Temperature Range	T_J, T_{STG}	-55 to $+175$	$^{\circ}\text{C}$
Maximum Lead Temp. For soldering Purposes, $\frac{1}{8}$ " from case for 5 seconds	T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

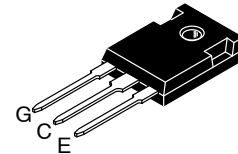
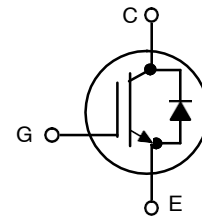
1. Value limit by bond wire.
2. $V_{CC} = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 300\text{ A}$, Inductive Load, 100% Tested.
3. Repetitive rating: pulse width limited by max. Junction temperature.



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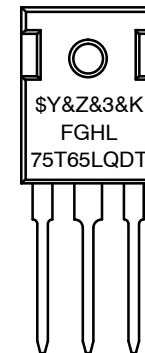
www.onsemi.com

V_{CES}	I_C	$V_{CE(sat)}$
650 V	75 A	1.15 V



TO-247-3L
CASE 340CX

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = 3-Digit Data Code
&K = 2-Digit Lot Traceability Code
FGHL75T65LQDT = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
FGHL75T65LQDT	TO-247-3L	30 Units / Rail

FGHL75T65LQDT

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Thermal Resistance Junction to Case, for IGBT	$R_{\theta JC}$	0.32	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Case, for Diode	$R_{\theta JC}$	0.6	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-emitter Breakdown Voltage, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	BV_{CES}	650	–	–	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\Delta BV_{CES} / \Delta T_J$	–	0.6	–	$\text{V}/^{\circ}\text{C}$
Collector-emitter Cut-off Current, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	I_{CES}	–	–	250	μA
Gate Leakage Current, Collector-emitter Short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	± 400	nA

ON CHARACTERISTICS

Gate-emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	$V_{GE(th)}$	3.0	4.5	6.0	V
Collector-emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 25^{\circ}\text{C}$	$V_{CE(sat)}$	–	1.15	1.35	V
	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 175^{\circ}\text{C}$		–	1.22	–	

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	15300	–	pF
Output Capacitance		C_{oes}	–	181	–	
Reverse Transfer Capacitance		C_{res}	–	68	–	
Gate Charge Total	$V_{CE} = 400\text{ V}, I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	793	–	nC
Gate to Emitter Charge		Q_{ge}	–	72	–	
Gate to Collector Charge		Q_{gc}	–	248	–	

SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on Delay Time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 37.5\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	45	–	ns
Rise Time		t_r	–	20	–	
Turn-off Delay Time		$t_{d(off)}$	–	608	–	
Fall Time		t_f	–	160	–	
Turn-on Switching Loss		E_{on}	–	0.78	–	mJ
Turn-off Switching Loss		E_{off}	–	1.36	–	
Total Switching Loss		E_{ts}	–	2.14	–	
Turn-on Delay Time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 75\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	48	–	ns
Rise Time		t_r	–	40	–	
Turn-off Delay Time		$t_{d(off)}$	–	568	–	
Fall Time		t_f	–	128	–	
Turn-on Switching Loss		E_{on}	–	1.88	–	mJ
Turn-off Switching Loss		E_{off}	–	2.38	–	
Total Switching Loss		E_{ts}	–	4.26	–	

FGHL75T65LQDT

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on Delay Time	$T_J = 175^\circ\text{C}$ $V_{CC} = 400\text{ V}$, $I_C = 37.5\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	44	–	ns
Rise Time		t_r	–	24	–	
Turn-off Delay Time		$t_{d(off)}$	–	680	–	
Fall Time		t_f	–	256	–	
Turn-on Switching Loss		E_{on}	–	1.54	–	mJ
Turn-off Switching Loss		E_{off}	–	2.11	–	
Total Switching Loss		E_{ts}	–	3.65	–	
Turn-on Delay Time	$T_J = 175^\circ\text{C}$ $V_{CC} = 400\text{ V}$, $I_C = 75\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	44	–	ns
Rise Time		t_r	–	44	–	
Turn-off Delay Time		$t_{d(off)}$	–	632	–	
Fall Time		t_f	–	184	–	
Turn-on Switching Loss		E_{on}	–	3.14	–	mJ
Turn-off Switching Loss		E_{off}	–	3.58	–	
Total Switching Loss		E_{ts}	–	6.72	–	

DIODE CHARACTERISTICS

Diode Forward Voltage	$I_F = 75\text{ A}$, $T_J = 25^\circ\text{C}$	V_F	–	1.65	2.1	V
	$I_F = 75\text{ A}$, $T_J = 175^\circ\text{C}$		–	1.55	–	
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$, $V_R = 400\text{ V}$, $I_F = 37.5\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}	–	105	–	μJ
Reverse Recovery Time		T_{rr}	–	59	–	ns
Reverse Recovery Charge		Q_{rr}	–	574	–	nC
Reverse Recovery Current		I_{rr}	–	20	–	A
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$, $V_R = 400\text{ V}$, $I_F = 75\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}	–	152	–	μJ
Reverse Recovery Time		T_{rr}	–	87	–	ns
Reverse Recovery Charge		Q_{rr}	–	794	–	nC
Reverse Recovery Current		I_{rr}	–	18	–	A
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$, $V_R = 400\text{ V}$, $I_F = 37.5\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}	–	550	–	μJ
Reverse Recovery Time		T_{rr}	–	119	–	ns
Reverse Recovery Charge		Q_{rr}	–	2154	–	nC
Reverse Recovery Current		I_{rr}	–	36	–	A
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$, $V_R = 400\text{ V}$, $I_F = 75\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}	–	764	–	μJ
Reverse Recovery Time		T_{rr}	–	145	–	ns
Reverse Recovery Charge		Q_{rr}	–	2947	–	nC
Reverse Recovery Current		I_{rr}	–	40	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

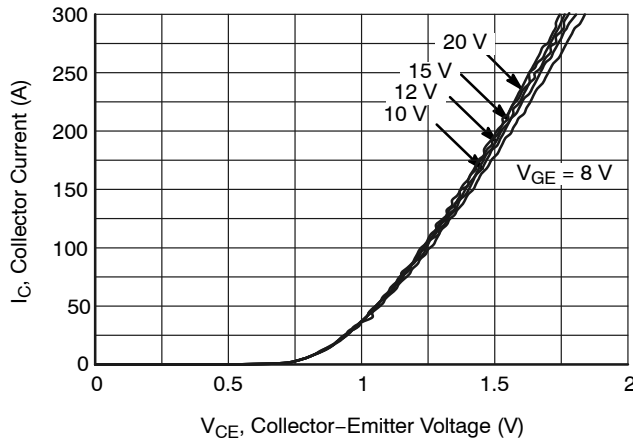


Figure 1. Typical Output Characteristics
($T_J = 25^\circ\text{C}$)

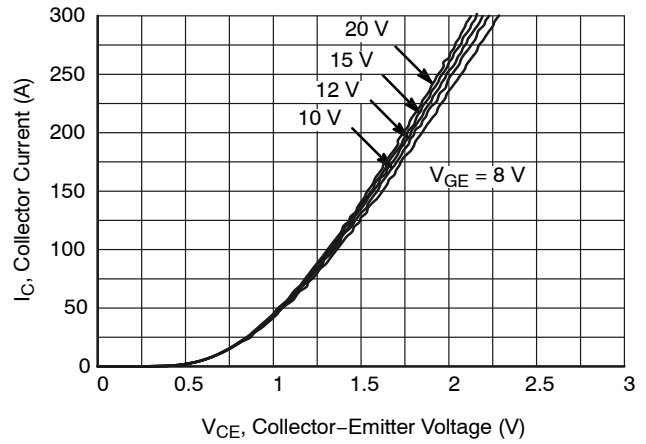


Figure 2. Typical Output Characteristics
($T_J = 175^\circ\text{C}$)

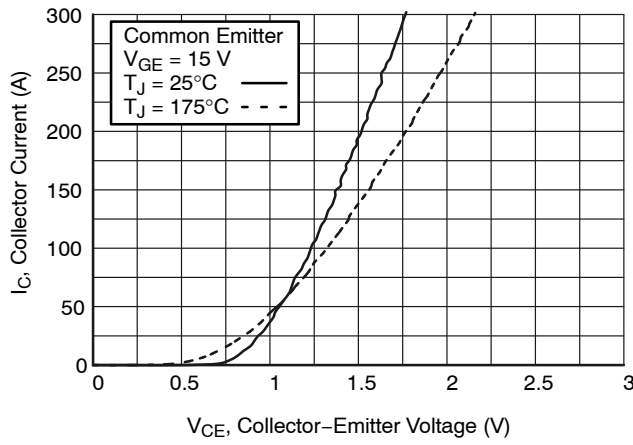


Figure 3. Typical Saturation Voltage Characteristics

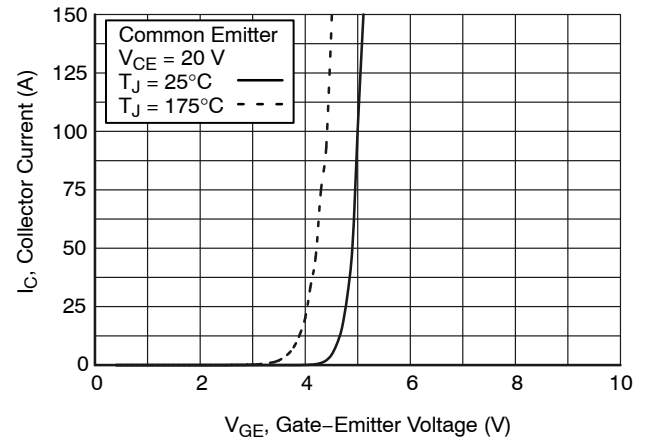


Figure 4. Typical Transfer Characteristics

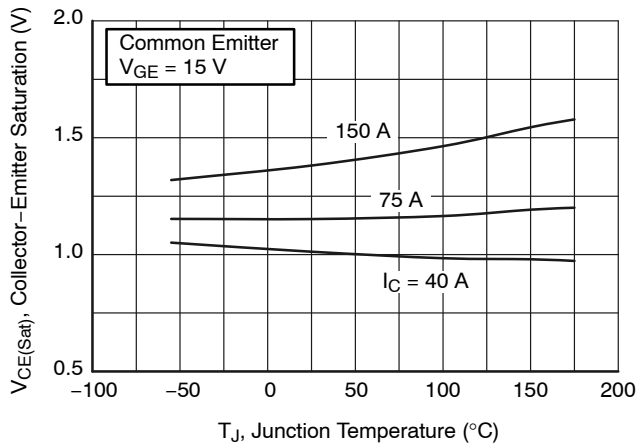


Figure 5. Saturation Voltage vs. Junction Temperature

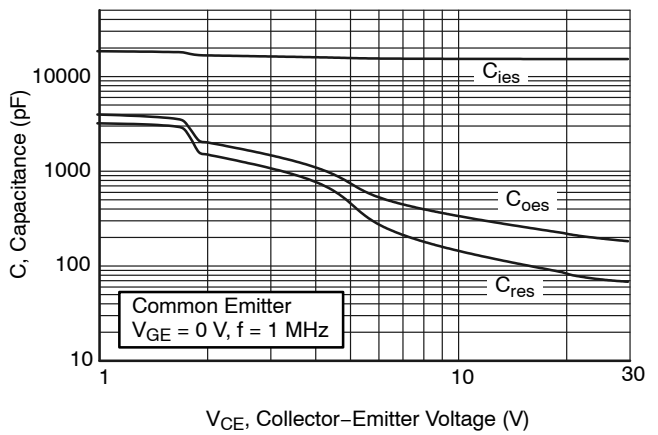


Figure 6. Capacitance Characteristics

TYPICAL CHARACTERISTICS (continued)

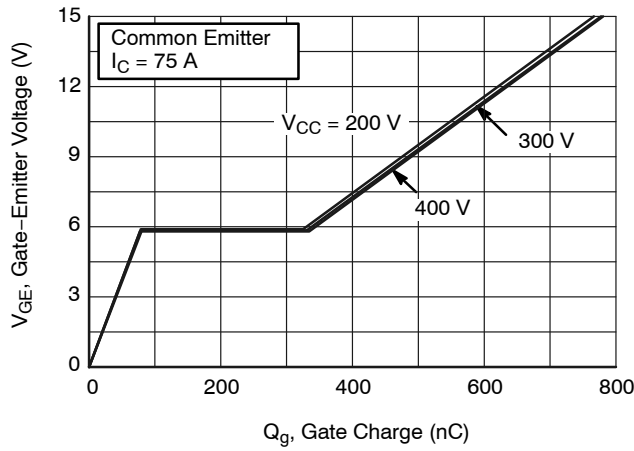


Figure 7. Gate Charge Characteristics

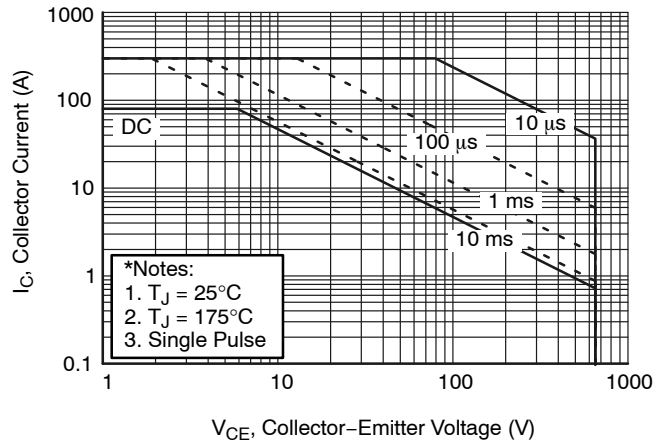


Figure 8. SOA Characteristics

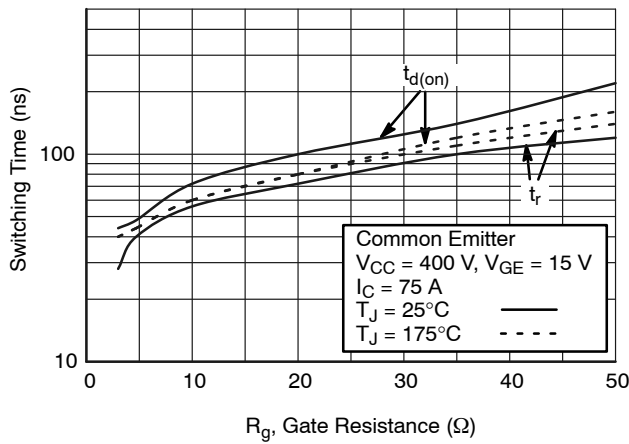


Figure 9. Turn-On Characteristics vs. Gate Resistance

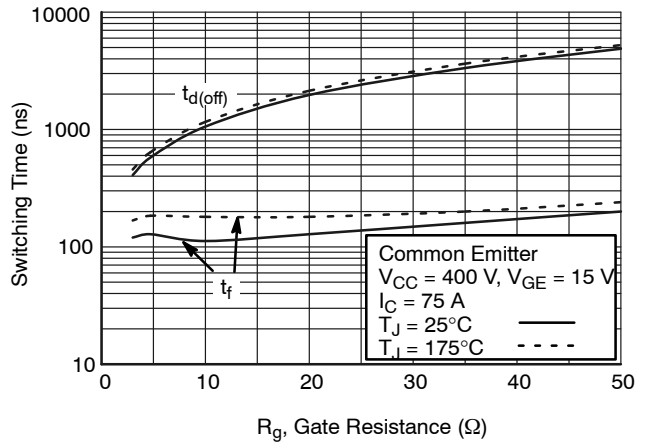


Figure 10. Turn-Off Characteristics vs. Gate Resistance

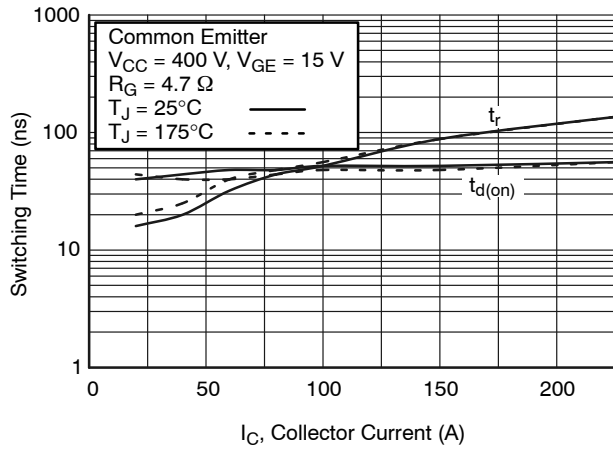


Figure 11. Turn-On Characteristics vs. Collector Current

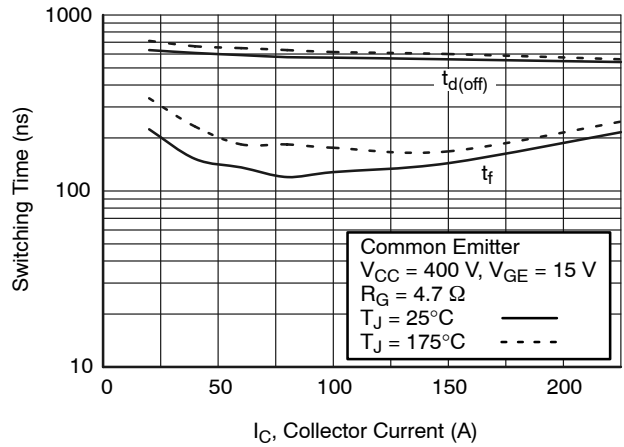


Figure 12. Turn-Off Characteristics vs. Collector Current

TYPICAL CHARACTERISTICS (continued)

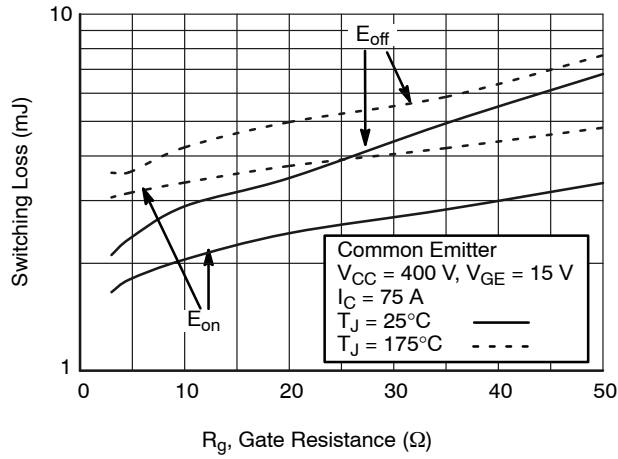


Figure 13. Switching Loss vs. Gate Resistance

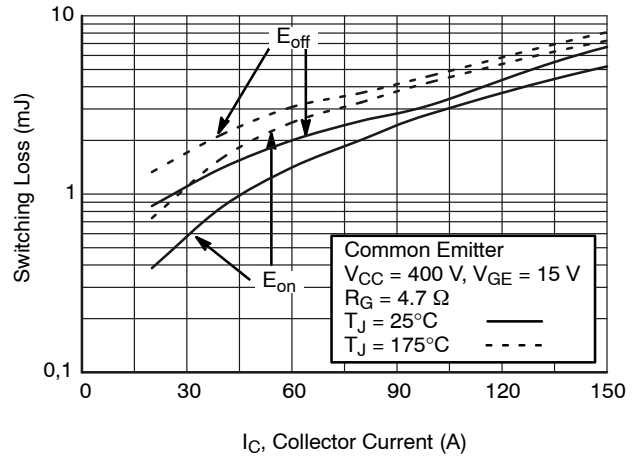


Figure 14. Switching Loss vs. Collector Current

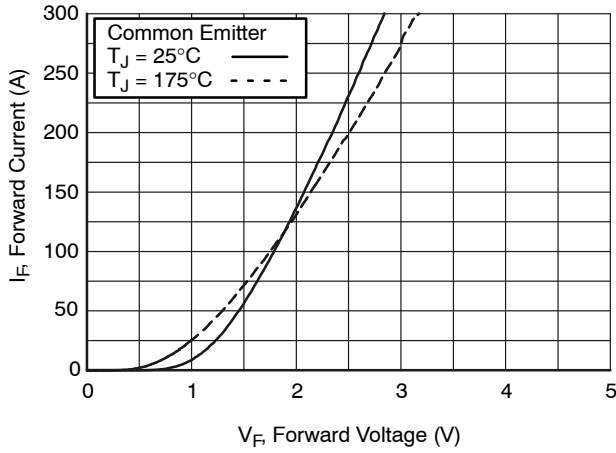


Figure 15. Forward Characteristics

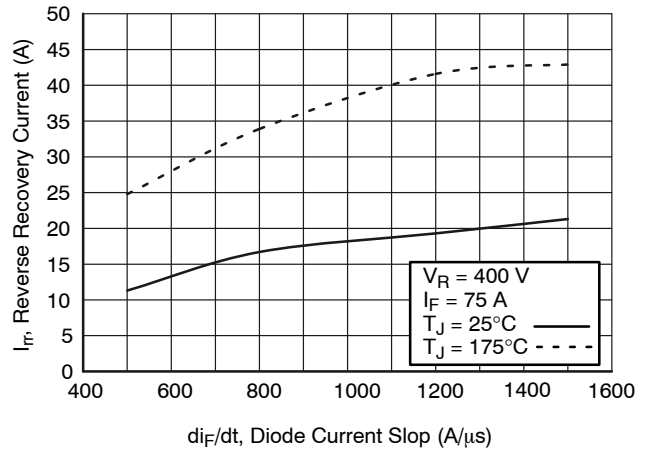


Figure 16. Reverse Recovery Current

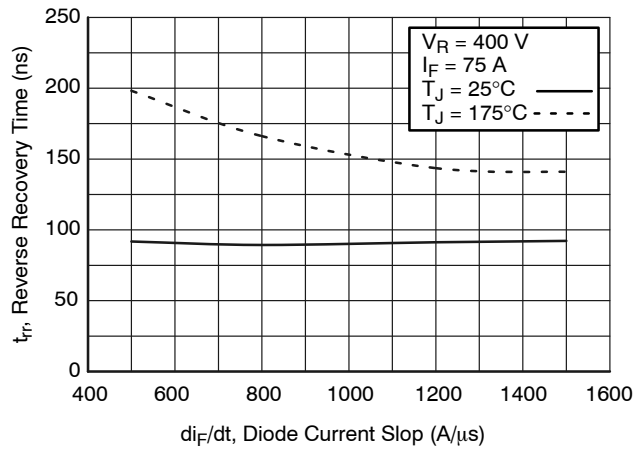


Figure 17. Reverse Recovery Time

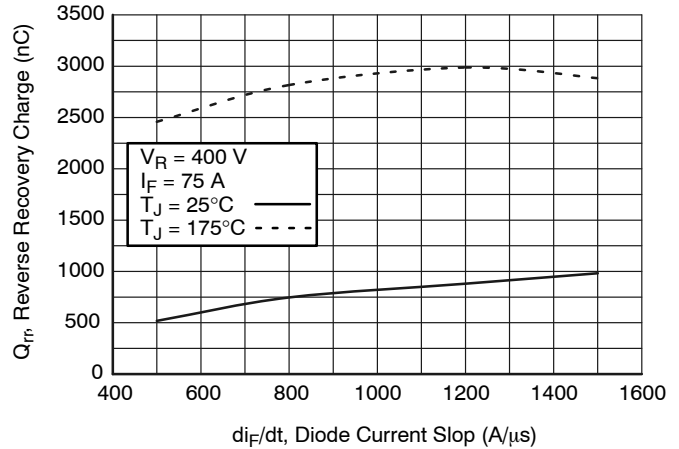


Figure 18. Stored Charge

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

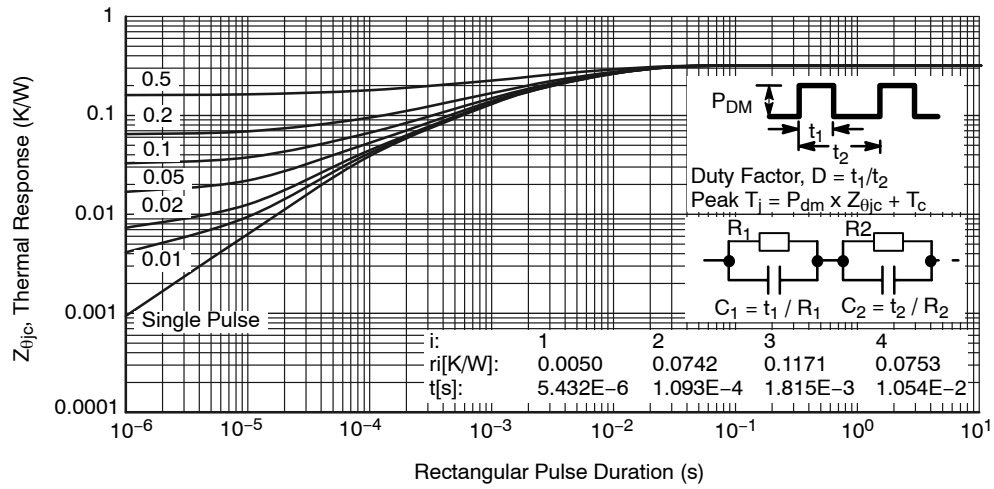


Figure 19. Transient Thermal Impedance of IGBT

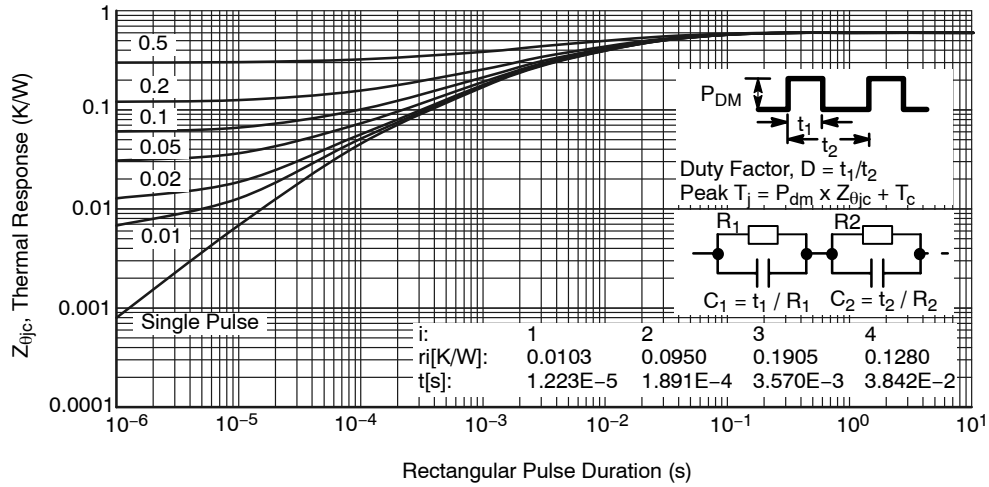


Figure 20. Transient Thermal Impedance of Diode

MECHANICAL CASE OUTLINE

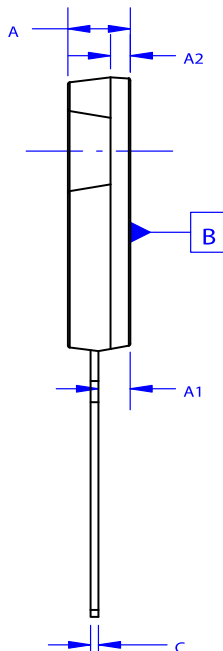
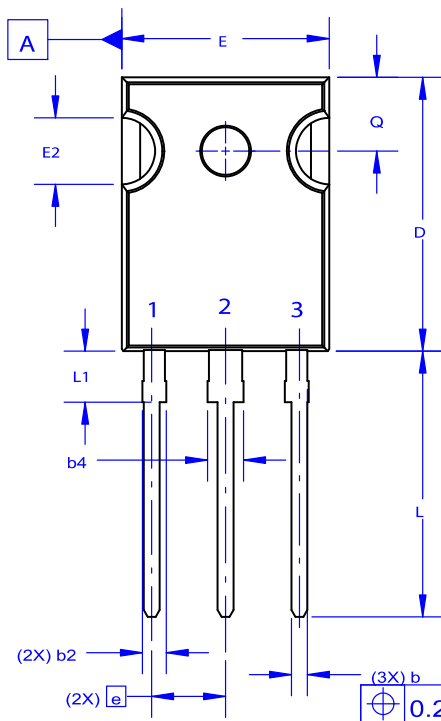
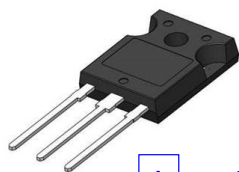
PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

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